# BAW56WT1G, SBAW56WT1G

# **Dual Switching Diode, Common Anode**

#### Features

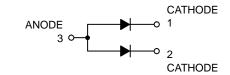
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and **PPAP** Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



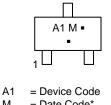
# **ON Semiconductor®**

www.onsemi.com





MARKING DIAGRAM



#### = Date Code\* Μ

= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

| Device     | Package            | Shipping <sup>†</sup> |
|------------|--------------------|-----------------------|
| BAW56WT1G  | SC–70<br>(Pb–Free) | 3,000 / Tape & Reel   |
| SBAW56WT1G | SC–70<br>(Pb–Free) | 3,000 / Tape & Reel   |

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### **MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ )

| Rating                     | Symbol                 | Max | Unit |
|----------------------------|------------------------|-----|------|
| Reverse Voltage            | V <sub>R</sub>         | 70  | V    |
| Forward Current            | ١ <sub>F</sub>         | 200 | mA   |
| Peak Forward Surge Current | I <sub>FM(surge)</sub> | 500 | mA   |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

| Characteristic   | Symbol                            | Max            | Unit  |
|--|-----------------------------------|----------------|-------|
| Total Device Dissipation FR-5 Board (Note 1)<br>$T_A = 25^{\circ}C$        | P <sub>D</sub>                    | 200            | mW    |
| Derate above 25°C  |                                   | 1.6            | mW/°C |
| Thermal Resistance, Junction-to-Ambient                                    | $R_{\thetaJA}$                    | 625            | °C/W  |
| Total Device Dissipation<br>Alumina Substrate (Note 2) $T_A = 25^{\circ}C$ | PD                                | 300            | mW    |
| Derate above 25°C  |                                   | 2.4            | mW/∘C |
| Thermal Resistance, Junction-to-Ambient                                    | $R_{\thetaJA}$                    | 417            | °C/W  |
| Junction and Storage Temperature   | T <sub>J</sub> , T <sub>stg</sub> | –55 to<br>+150 | °C    |

1. FR-5 = 1.0  $\times$  0.75  $\times$  0.062 in.

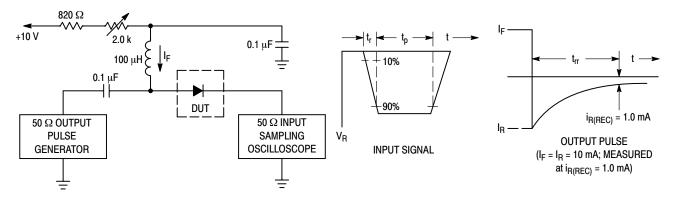
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

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#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

| Characteristic  | Symbol            | Min              | Max                        | Unit |  |
|---|-------------------|------------------|----------------------------|------|--|
| OFF CHARACTERISTICS   |                   |                  |                            |      |  |
| Reverse Breakdown Voltage $(I_{(BR)} = 100 \ \mu A)$  | V <sub>(BR)</sub> | 70               | _                          | V    |  |
| Reverse Voltage Leakage Current<br>$(V_R = 25 \text{ V}, \text{ T}_J = 150^{\circ}\text{C})$<br>$(V_R = 70 \text{ V})$<br>$(V_R = 70 \text{ V}, \text{ T}_J = 150^{\circ}\text{C})$ | I <sub>R</sub>    | -<br>-<br>-      | 30<br>2.5<br>50            | μΑ   |  |
| Diode Capacitance<br>( $V_R = 0, f = 1.0 \text{ MHz}$ )   | CD                | _                | 2.0                        | pF   |  |
| Forward Voltage<br>$(I_F = 1.0 \text{ mA})$<br>$(I_F = 10 \text{ mA})$<br>$(I_F = 50 \text{ mA})$<br>$(I_F = 150 \text{ mA})$   | VF                | -<br>-<br>-<br>- | 715<br>855<br>1000<br>1250 | mV   |  |
| Reverse Recovery Time ( $I_F = I_R = 10 \text{ mA}, R_L = 100 \Omega, I_{R(REC)} = 1.0 \text{ mA}$ ) (Figure 1)   | t <sub>rr</sub>   | -                | 6.0                        | ns   |  |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (I<sub>F</sub>) of 10 mA. 2. Input pulse is adjusted so I<sub>R(peak)</sub> is equal to 10 mA. 3. t<sub>p</sub> » t<sub>rr</sub>

Figure 1. Recovery Time Equivalent Test Circuit

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### **TYPICAL CHARACTERISTICS**

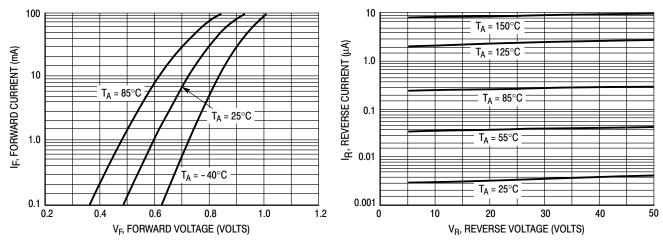


Figure 2. Forward Voltage

Figure 3. Leakage Current

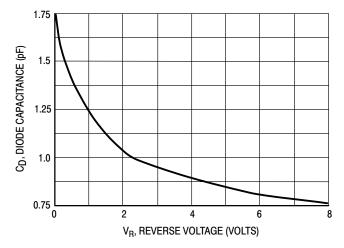
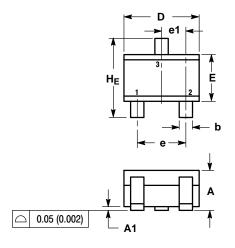


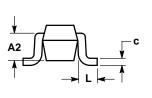
Figure 4. Capacitance

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#### PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 **ISSUE N** 





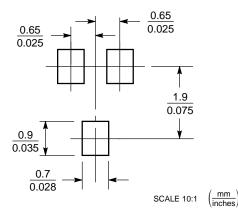
NOTES: DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: INCH.

|     | MILLIMETERS |      |      | INCHES    |       |       |
|-----|-------------|------|------|-----------|-------|-------|
| DIM | MIN         | NOM  | MAX  | MIN       | NOM   | MAX   |
| Α   | 0.80        | 0.90 | 1.00 | 0.032     | 0.035 | 0.040 |
| A1  | 0.00        | 0.05 | 0.10 | 0.000     | 0.002 | 0.004 |
| A2  | 0.70 REF    |      |      | 0.028 REF |       |       |
| b   | 0.30        | 0.35 | 0.40 | 0.012     | 0.014 | 0.016 |
| С   | 0.10        | 0.18 | 0.25 | 0.004     | 0.007 | 0.010 |
| D   | 1.80        | 2.10 | 2.20 | 0.071     | 0.083 | 0.087 |
| E   | 1.15        | 1.24 | 1.35 | 0.045     | 0.049 | 0.053 |
| е   | 1.20        | 1.30 | 1.40 | 0.047     | 0.051 | 0.055 |
| e1  | 0.65 BSC    |      |      | 0.026 BSC |       |       |
| L   | 0.20        | 0.38 | 0.56 | 0.008     | 0.015 | 0.022 |
| HE  | 2.00        | 2.10 | 2.40 | 0.079     | 0.083 | 0.095 |

#### STYLE 4: PIN 1. CATHODE 2. CATHODE

3. ANODE

#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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